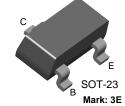


MMBTH10RG

NPN RF Transistor

- This device is designed for use in low noise UHF/VHF amplifiers, with collector currents in the 100 μA to 20 mA range in common emitter or common base mode of operations, and in low frequency drift, high output UHF oscillators.
- · Sourced from process 42.



1. Base 2. Emitter 3. Collector

Absolute Maximum Ratings* T_a=25°C unless otherwise noted

Symbol	Parameter	Ratings	Units
V _{CEO}	Collector-Emitter Voltage	40	V
V _{CBO}	Collector-Base Voltage	40	V
V _{EBO}	Emitter-Base Voltage	4.0	V
I _C	Collector Current - Continuous	50	mA
T _J , T _{STG}	Operating and Storage Junction Temperature Range	-55 ~ 150	°C

^{*} This ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

These rating are based on a maximum junction temperature of 150 degrees C.
These are steady limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Electrical Characteristics T_a=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units	
Off Charac	teristics					
V _{(BR)CEO}	Collector-Emitter Sustaining Voltage *	I _C = 1.0 mA, I _B = 0	40		V	
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_C = 10 \mu\text{A}, I_E = 0$	40		V	
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_E = 1.0 \mu A, I_C = 0$	4.0		V	
I _{CBO}	Collector Cutoff Current	$V_{CB} = 30 \text{ V, I}_{E} = 0$		100	nA	
On Characteristics						
h _{FE}	DC Current Gain	I _C = 1.0 mA, V _{CE} = 6.0 V	50	120	V	
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 10 mA, I _B = 5.0 mA		0.2	V	
	al Characteristics					
f _T	Current Gain - Bandwidth Product	I _C = 2.0 mA, V _{CE} = 10 V, f = 100 MHz	450		MHz	
C _{cb}	Collector-Base Capacitance	V _{CB} = 10 V, I _E = 0, f = 1.0 MHz		0.6	pF	
rb'Cc	Collector Base Time Constant	$I_C = 5.0 \text{ mA}, V_{CB} = 10 \text{ V},$ f = 79.8 MHz		12	pS	

^{*} Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%

Thermal Characteristics T_a=25°C unless otherwise noted

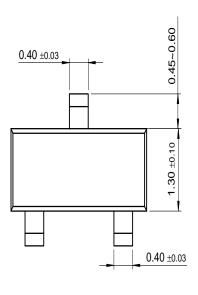
Symbol	Parameter	Max.	Units
P _D	Total Device Dissipation	225	mW
	Derate above 25°C	1.8	mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	556	°C/W

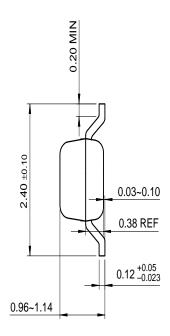
^{*}Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

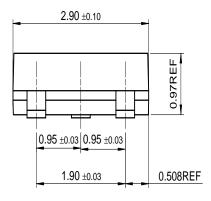
©2004 Fairchild Semiconductor Corporation Rev. A, April 2004

Package Dimensions

SOT-23







Dimensions in Millimeters

TRADEMARKS

The following are registered and unregistered trademarks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

ACE	X TM	FACT Quiet Series™	ImpliedDisconnect™	PACMAN™	SPM™
Acti	veArray™	FAST [®]	ISOPLANAR™	POP™	Stealth™
Bott	omless™	FASTr™	LittleFET™	Power247™	SuperFET™
Coo	IFET™	FPS™	MICROCOUPLER™	PowerSaver™	SuperSOT™-3
CR	OSSVOLT™	FRFET™	MicroFET™	PowerTrench [®]	SuperSOT™-6
DO	ЛЕ™	GlobalOptoisolator™	MicroPak™	QFET [®]	SuperSOT™-8
Eco	SPARK™	GTO™	MICROWIRE™	QS TM	SyncFET™
E^2C	MOS™	HiSeC™	MSX TM	QT Optoelectronics™	TinyLogic [®]
EnS	igna™	I ² C TM	MSXPro™	Quiet Series™	TINYOPTO™
FAC	T™.	i-Lo™	OCX^{TM}	RapidConfigure™	TruTranslation™
Acro	ss the board.	. Around the world.™	OCXPro™	RapidConnect™	UHC™
The Power Franchise®		OPTOLOGIC [®]	SILENT SWITCHER®	UltraFET [®]	
Programmable Active Droop™		OPTOPLANAR™	SMART START™	VCX TM	
	· ·				

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used herein:

- 1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user.
- 2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.